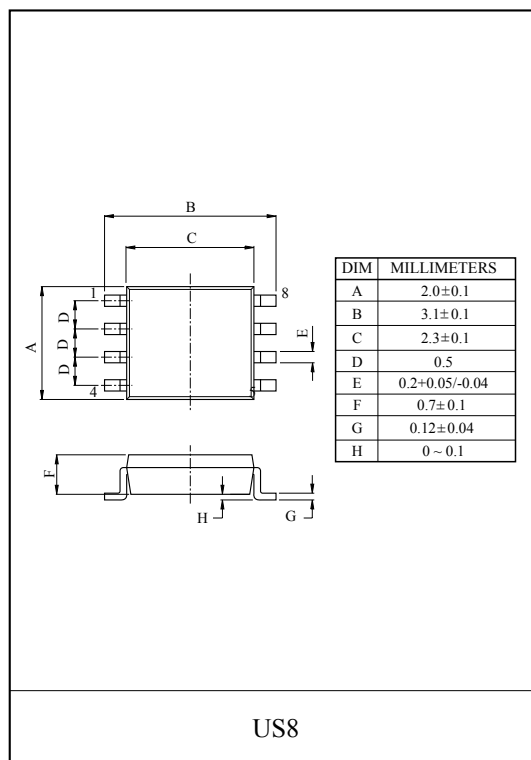
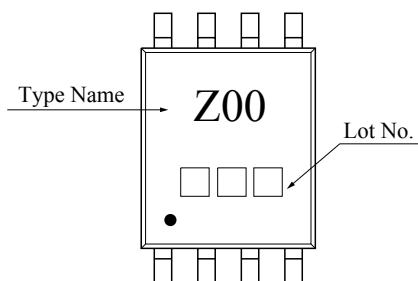


2 INPUT NAND GATE

FEATURES

- High output drive : $\pm 24\text{mA}(\text{min.}) @ V_{CC}=3\text{V}$.
- Super high speed operation : $\text{tpd } 2.4\text{ns}(\text{typ.}) @ V_{CC}=5\text{V}, 50\text{pF}$.
- Operation voltage range : $V_{CC(\text{opr})}=1.65\sim 5.5\text{V}$.
- Latch-up performance : $\pm 500\text{mA}$ or more
- ESD performance : $\pm 200\text{V}$ or more (EIAJ)
 $\pm 2000\text{V}$ or more (MIL)
- Power down protection is provided on all inputs and outputs.

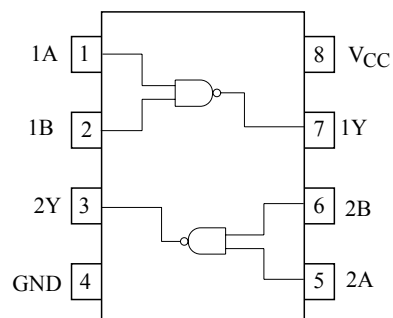
MARKING



MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~6	V
DC Input Voltage	V_{IN}	-0.5~6	V
DC Output Voltage	V_{OUT}	-0.5~6	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	-20	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	200	mW
Storage Temperature Range	T_{stg}	-65 ~ 150	°C
Lead Temperature (10s)	T_L	260	°C

PIN CONNECTION(TOP VIEW)



KIC7WZ00FK

Truth Table

A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

Logic Diagram



Recommended Operating Conditions

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	1.65~5.5	V
		1.5~5.5 (Note1)	
Input Voltage	V _{IN}	0~5.5	V
Output Voltage	V _{OUT}	0~5.5 (Note2)	V
		0~V _{CC} (Note3)	
Operating Temperature	T _{opr}	-40~85	℃
Input Rise and Fall Time	d _t /d _v	0~20 (V _{CC} =1.8V±0.15V, 2.5V±0.2V)	ns/V
		0~10 (V _{CC} =3.3V±0.3V)	
		0~5 (V _{CC} =5.5V±0.5V)	

Note1 : Data retention only.

Note2 : V_{CC}=0V.

Note3 : High or low state

KIC7WZ00FK

ELECTRICAL CHARACTERISTICS

DC Characteristics

CHARACTERISTIC		SYMBOL	TEST CONDITION		Ta=25℃			Ta=-40~85℃		UNIT	
				V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.		
Input Voltage	High Level	V _{IH}	-	1.65~1.95	$0.75 \times V_{CC}$	-	-	$0.75 \times V_{CC}$	-	V	
				2.3~5.5	$0.7 \times V_{CC}$	-	-	$0.7 \times V_{CC}$	-		
	Low Level	V _{IL}	-	1.65~1.95	-	-	$0.25 \times V_{CC}$	-	$0.25 \times V_{CC}$		
				2.3~5.5	-	-	$0.3 \times V_{CC}$	-	$0.3 \times V_{CC}$		
Output Voltage	High Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} =-100μA	1.65	1.55	1.65	-	1.55	-	V
					2.3	2.2	2.3	-	2.2	-	
					3.0	2.9	3.0	-	2.9	-	
					4.5	4.4	4.5	-	4.4	-	
				I _{OH} =-4mA	1.65	1.29	1.52	-	1.29	-	
				I _{OH} =-8mA	2.3	1.9	2.15	-	1.9	-	
				I _{OH} =-16mA	3.0	2.4	2.8	-	2.4	-	
				I _{OH} =-24mA	3.0	2.3	2.68	-	2.3	-	
				I _{OH} =-32mA	4.5	3.8	4.2	-	3.8	-	
	Low Level	V _{OL}	V _{IN} =V _{IL}	I _{OH} =100μA	1.65	-	0	0.1	-	0.1	V
					2.3	-	0	0.1	-	0.1	
					3.0	-	0	0.1	-	0.1	
					4.5	-	0	0.1	-	0.1	
				I _{OH} =4mA	1.65	-	0.08	0.24	-	0.24	
				I _{OH} =8mA	2.3	-	0.1	0.3	-	0.3	
				I _{OH} =16mA	3.0	-	0.15	0.4	-	0.4	
				I _{OH} =24mA	3.0	-	0.22	0.55	-	0.55	
				I _{OH} =32mA	4.5	-	0.22	0.55	-	0.55	
Input Leakage Current		I _{IN}	V _{IN} =5.5V or GND	0~5.5	-	-	±1	-	±10	μA	
Power Off Leakage Current		I _{OFF}	V _{IN} or V _{OUT} =5.5V	0.0	-	-	1	-	10	μA	
Quiescent Supply Current		I _{CC}	V _{IN} =5.5V or GND	1.65~5.5	-	-	1	-	10	μA	

AC Characteristics (unless otherwise specified, Input : t_r=t_f=3ns)

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta=25℃			Ta=-40~85℃		UNIT
			V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation delay time	t _{PLH} t _{PHL}	C _L =15pF, R _L =1MΩ	1.8±0.15	2.0	5.3	9.6	2.0	9.8	ns
			2.5±0.2	1.2	3.2	5.3	1.2	5.7	
			3.3±0.3	0.8	2.4	3.7	0.8	4.0	
			5.0±0.5	0.5	1.9	2.9	0.5	3.2	
		C _L =50pF, R _L =500Ω	3.3±0.3	1.2	3.0	4.6	1.2	4.9	ns
			5.0±0.5	0.8	2.4	3.6	0.8	3.9	
Input Capacitance	C _{IN}	-	0~5.5	-	3.0	-	-	-	pF
Power Dissipation Capacitance	C _{PD}	(Note)	3.3	-	22	-	-	-	pF
			5.5	-	32	-	-	-	

Note : C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation : $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$